

FP216

1:Base

2:Collector

4:Collector

6:Collector

7:Collector

SANYO:PCP5 (Bottom view)

5:Base

3:Emitter Common

0.2min

NPN Epitaxial Planar Silicon Transistor

LCD Backlight Drive Applications

[FP216]

0

(0.5)

Package Dimensions

unit:mm

2097B

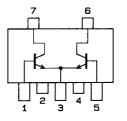
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4.25may

Features

- · Composite type with 2 transistors contained in the PCP5 package currently in use, improving the mounting efficiency greatly.
- The FP216 is composed of two chips, each being equivalent to the 2SC3646, placed in one package.

Electrical Connection



1:Base 2:Collector 3:Emitter Common 4:Collector 5:Base 6:Collector 7:Collector

(Top view)

Specifications

Absolute Maximum Ratings at Ta = 25°C

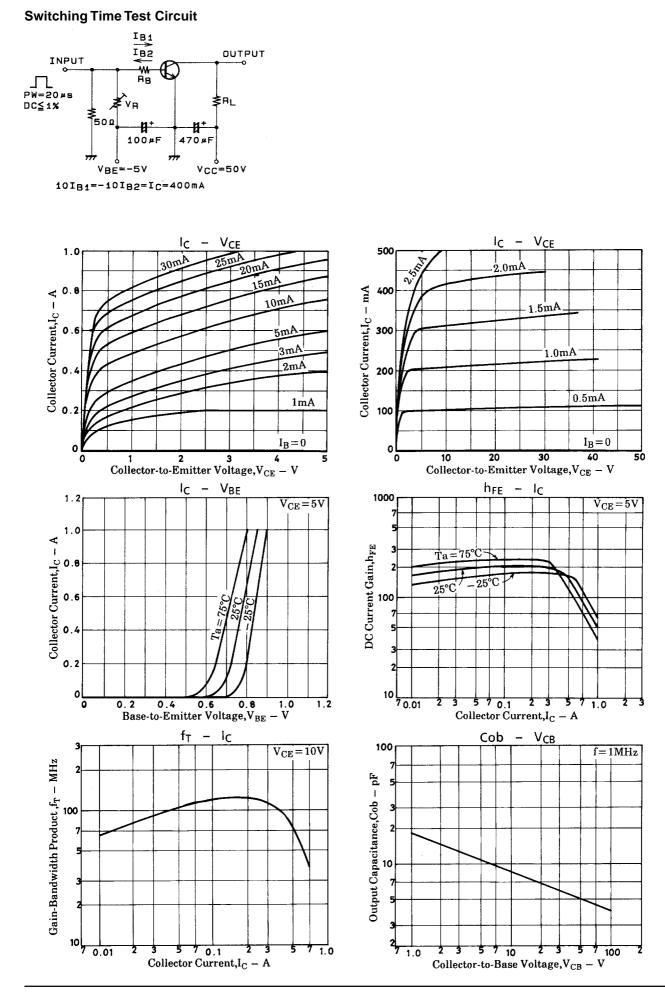
Parameter Symbol Conditions Ratings Unit Collector-to-Base Voltage V 120 VCBO 100 V Collector-to-Emitter Voltage VCEO Emitter-to-Base Voltage V VEBO 6 Collector Current IC 1 А Collector Current (Pulse) **ICP** 2 А Base Current I_B 200 mΑ PC **Collector Dissipation** Mounted on ceramic board (250mm²×0.8mm) 1 unit 0.8 W **Total Dissipation** PΤ Mounted on ceramic board (250mm²×0.8mm) 1.1 W Junction Temperature Тj 150 °C Storage Temperature Tstg -55 to +150 °C

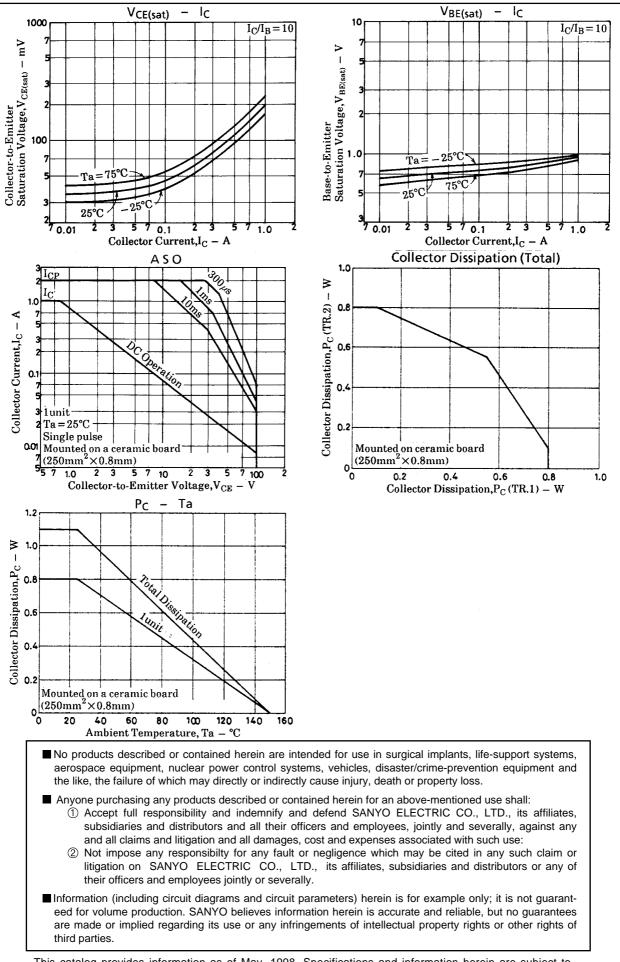
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditons	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =100V, I _E =0			100	nA
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0			100	nA
DC Current Gain	hFE	V _{CE} =5V, I _C =100mA	140		400	
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =100mA		120		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		8.5		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C =400mA, I _B =40mA		100	400	mV
B-E Saturation Voltage	V _{BE(sat)}	I _C =400mA, I _B =40mA		0.85	1.2	V
C-B Breakdown Voltage	V _(BR) CBO	I _C =10µA, I _E =0	120			V
C-E Breakdown Voltage	V(BR)CEO	I _C =1mA, R _{BE} =∞	100			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6			V
Turn-ON Time	ton	See specified Test Circuit		80		ns
Storage Time	tstg	See specified Test Circuit		850		ns
Fall Time	tf	See specified Test Circuit		50		ns

Marking:216

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This catalog provides information as of May, 1998. Specifications and information herein are subject to change without notice.